Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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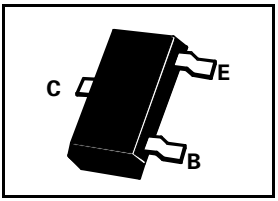
SOT23 PNP SILICON PLANAR HIGH GAIN MEDIUM POWER TRANSISTOR

FMMTL720

ISSUE 1 – DECEMBER 1997

FEATURES

Very low equivalent on-resistance; $\mathbf{R_{CE(sat)}}$=210mΩ at 1.5A



COMPLEMENTARY TYPE – FMMTL619

PARTMARKING DETAIL – L70

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-1	A
Peak Pulse Current	I_{CM}	-1.5	A
Base Current	I_B	-200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	-500	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

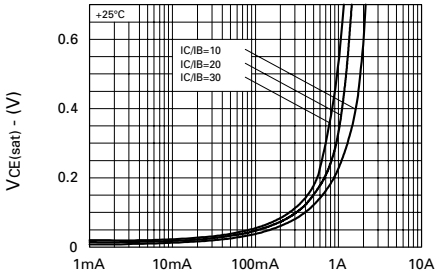
FMMTL720

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

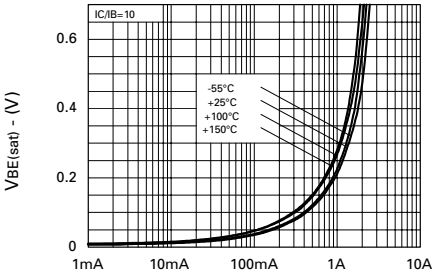
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	-95		V	I_C=-100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40	-70		V	I_C=-10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-8.8		V	I_E=-100μA
Collector Cut-Off Current	I_{CBO}			-10	nA	V_{CB}=-35V
Emitter Cut-Off Current	I_{EBO}			-10	nA	V_{EB}=-4V
Collector Cut-Off Current	I_{CES}			-10	nA	V_{CE}=-35V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-40 -150 -225	-50 -200 -300	mV mV mV	I_C=-100mA, I_B=-10mA* I_C=-500mA, I_B=-20mA* I_C=-1A, I_B=-100mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-985	-1100	mV	I_C=-1A, I_B=-100mA*
Base-Emitter Turn On Voltage	$V_{BE(on)}$		-825	-1000	mV	I_C=-1A, V_{CE}=-5V*
Static Forward Current Transfer Ratio	h_{FE}	300 300 200 150 75	490 450 340 250 150			I_C=-10mA, V_{CE}=-5V I_C=-100mA, V_{CE}=-5V* I_C=-0.5A, V_{CE}=-5V* I_C=-1A, V_{CE}=-5V* I_C=-1A, V_{CE}=-2V*
Transition Frequency	f_T				MHz	I_C=-50mA, V_{CE}=-10V f=100MHz
Collector-Base Breakdown Voltage	C_{obo}				pF	V_{CB}=-10V, f=1MHz
Switching times	t_{on} t_{off}		61 61		ns ns	I_C=-1A, V_{CC}=-10V I_{B1}=I_{B2}=-10mA

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

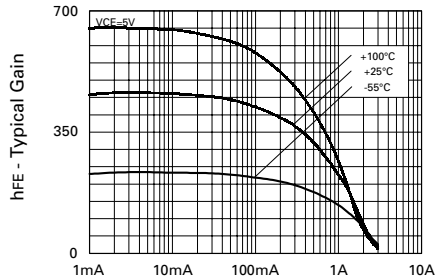
TYPICAL CHARACTERISTICS



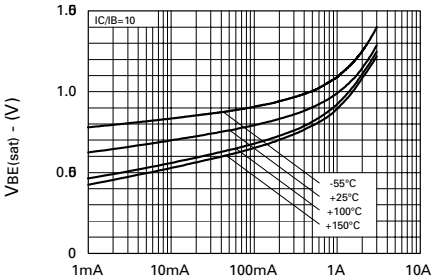
VCE(sat) v IC



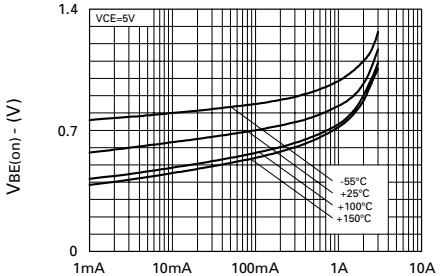
VBE(sat) v IC



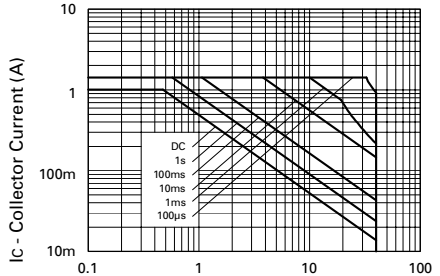
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area